

Title (en)
MONOLITHIC WHITE LIGHT-EMITTING DIODE

Title (de)
MONOLITHISCHE WEISSE LEUCHTDIODE

Title (fr)
DIODE ELECTROLUMINESCENTE BLANCHE MONOLITHIQUE

Publication
EP 1994571 A1 20081126 (FR)

Application
EP 07731714 A 20070309

Priority
• FR 2007050898 W 20070309
• FR 0650842 A 20060313

Abstract (en)
[origin: WO2007104884A1] The invention relates to a device comprising a matrix (13) made of III-V nitride, said matrix (13) comprising at least an active first portion (3, 4, 12) through which an electrical current (11) passes and at least a passive second portion (5, 6) through which no electrical current passes, said matrix comprising at least a first zone (3) forming a first quantum confinement region made of a III-V nitride, said first zone (3) being positioned in said active first portion (3, 4, 12), and at least a second zone (5) forming a second quantum confinement region made of III-V nitride, characterized in that said second zone is positioned in said passive portion of said matrix (5, 6).

IPC 8 full level
H01L 33/50 (2010.01); **H01L 33/08** (2010.01)

CPC (source: EP US)
H01L 33/08 (2013.01 - EP US); **H01L 27/15** (2013.01 - EP US)

Citation (search report)
See references of WO 2007104884A1

Designated contracting state (EPC)
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IS IT LI LT LU LV MC MT NL PL PT RO SE SI SK TR

DOCDB simple family (publication)
FR 2898434 A1 20070914; FR 2898434 B1 20080523; EP 1994571 A1 20081126; JP 2009530803 A 20090827; KR 20080104368 A 20081202; US 2009101934 A1 20090423; US 2011045623 A1 20110224; US 8470618 B2 20130625; WO 2007104884 A1 20070920

DOCDB simple family (application)
FR 0650842 A 20060313; EP 07731714 A 20070309; FR 2007050898 W 20070309; JP 2008558861 A 20070309; KR 20087024979 A 20081013; US 22503907 A 20070309; US 88286810 A 20100915